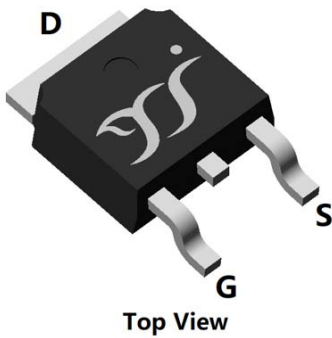
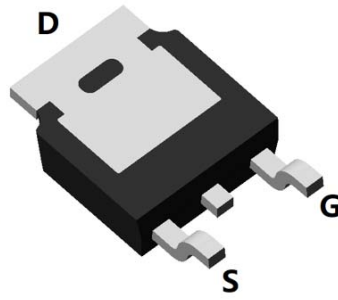


## N-Channel Enhancement Mode Field Effect Transistor

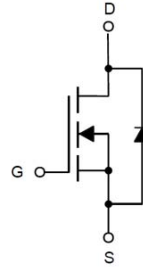


Top View



Bottom View

**TO-252**



### Product Summary

- $V_{DS}$  100V
- $I_D$  45A
- $R_{DS(ON)}$ ( at  $V_{GS}=10V$ )  $<17m\Omega$
- $R_{DS(ON)}$ ( at  $V_{GS}=4.5V$ )  $<21.5m\Omega$
- 100% UIS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Low  $R_{DS(on)}$  & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery
- Part no. with suffix "Q" means AEC-Q101 qualified

### Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply
- DC-DC convertor

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	100	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25^\circ C$	$I_D$	7	A
	$T_A=100^\circ C$		4.5	
	$T_C=25^\circ C$		45	
	$T_C=100^\circ C$		28	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	180	A
Avalanche energy <sup>B</sup>		EAS	90	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25^\circ C$	$P_D$	2.5	W
	$T_A=100^\circ C$		1	
	$T_C=25^\circ C$		73	
	$T_C=100^\circ C$		29	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	$^\circ C$



# YJD45G10AQ

## ■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>D</sup>	Steady-State	R <sub>θJA</sub>	40	50	°C/W
Thermal Resistance Junction-to-Case	Steady-State	R <sub>θJC</sub>	1.4	1.7	

## ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJD45G10AQ	F1	YJD45G10A	2500	/	25000	13"Reel



# YJD45G10AQ

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	100	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V	-	-	1	μA
		V <sub>DS</sub> =100V, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C	-	-	100	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.8	2.5	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =22.5A	-	14	17	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	17	21.5	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =22.5A, V <sub>GS</sub> =0V	-	0.9	1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>		-	-	45	A
Gate resistance	R <sub>G</sub>	f=1MHz, Open drain	-	1.4	-	Ω
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V, f=1MHz	-	1165	-	pF
Output Capacitance	C <sub>oss</sub>		-	265	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	8	-	
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =50V, I <sub>D</sub> =22.5A	-	19	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	6	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	3	-	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =22.5A, di/dt=100A/us	-	45	-	nC
Reverse Recovery Time	t <sub>rr</sub>		-	40	-	ns
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =50V, I <sub>D</sub> =22.5A R <sub>GEN</sub> =2.2Ω	-	40	-	ns
Turn-on Rise Time	t <sub>r</sub>		-	12	-	
Turn-off Delay Time	t <sub>D(off)</sub>		-	55	-	
Turn-off fall Time	t <sub>f</sub>		-	16	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T<sub>J</sub>=25°C, V<sub>DD</sub>=50V, V<sub>G</sub>=10V, R<sub>G</sub>=25Ω, L=0.5mH, I<sub>AS</sub>=19A.

C. P<sub>q</sub> is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R<sub>θJA</sub> is measured with the device mounted on the minimum recommend pad size, in the still air environment with T<sub>A</sub>=25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



# YJD45G10AQ

## Typical Electrical and Thermal Characteristics Diagrams

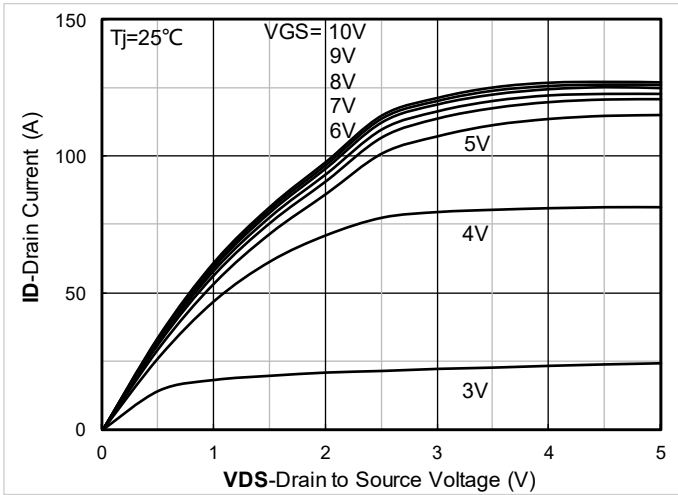


Figure 1. Output Characteristics

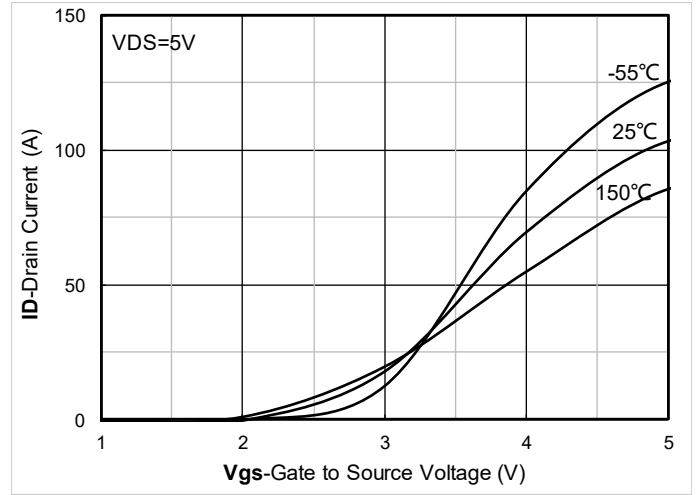


Figure 2. Transfer Characteristics

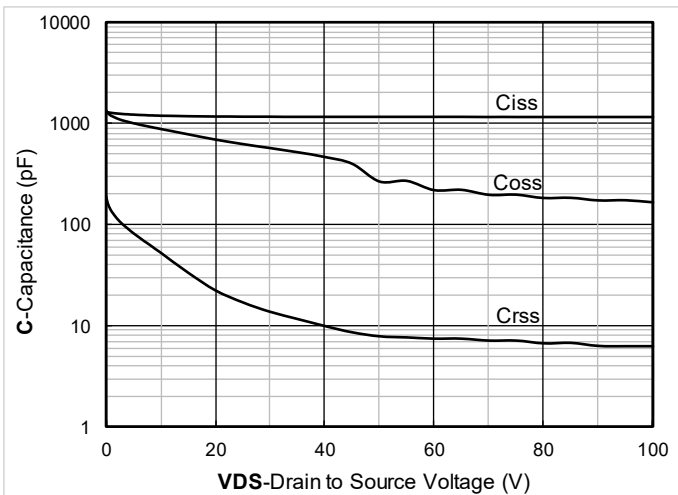


Figure 3. Capacitance Characteristics

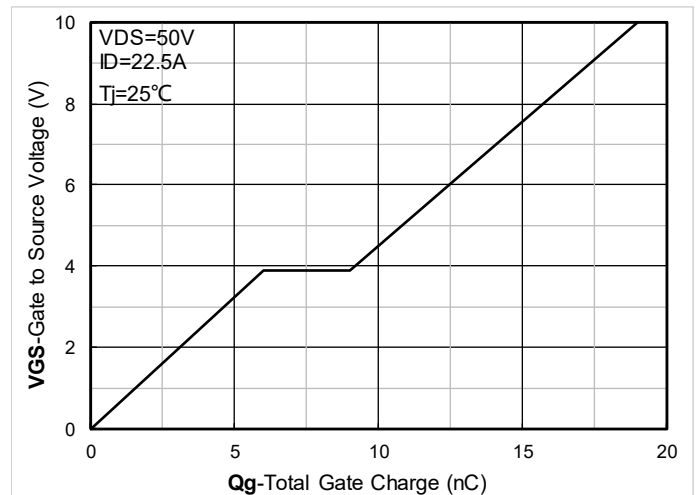


Figure 4. Gate Charge

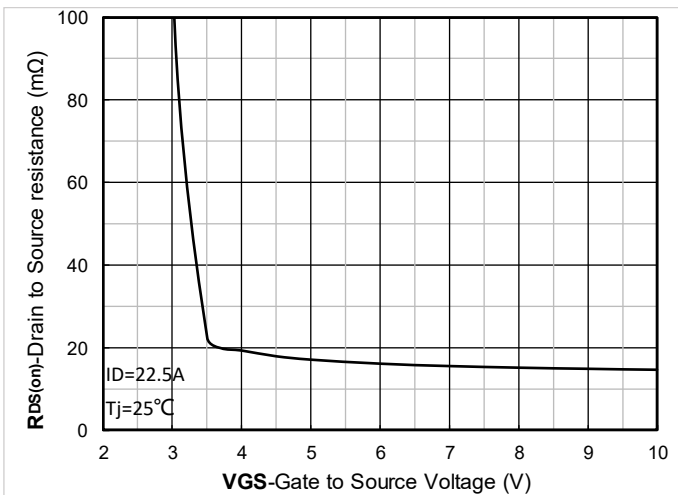


Figure 5. On-Resistance vs Gate to Source Voltage

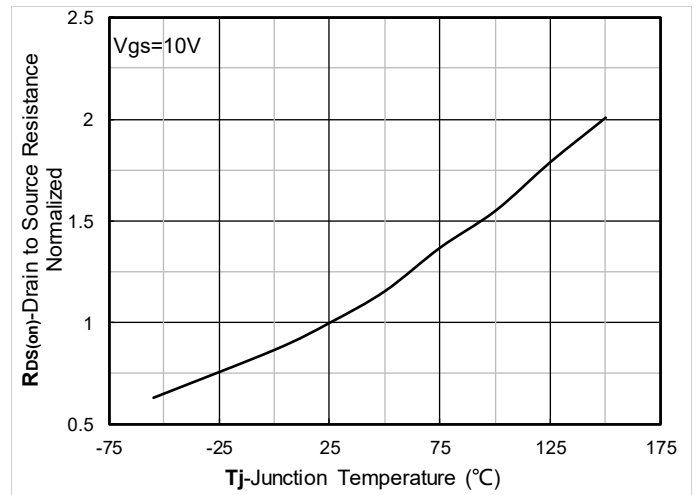


Figure 6. Normalized On-Resistance



# YJD45G10AQ

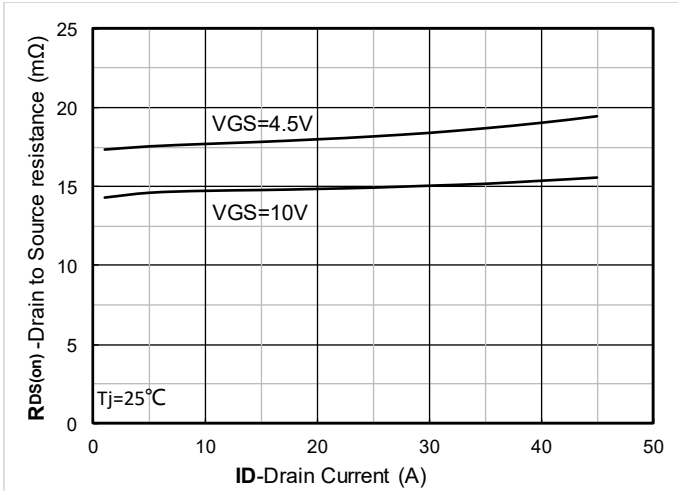


Figure 7.  $R_{DS(on)}$  VS Drain Current

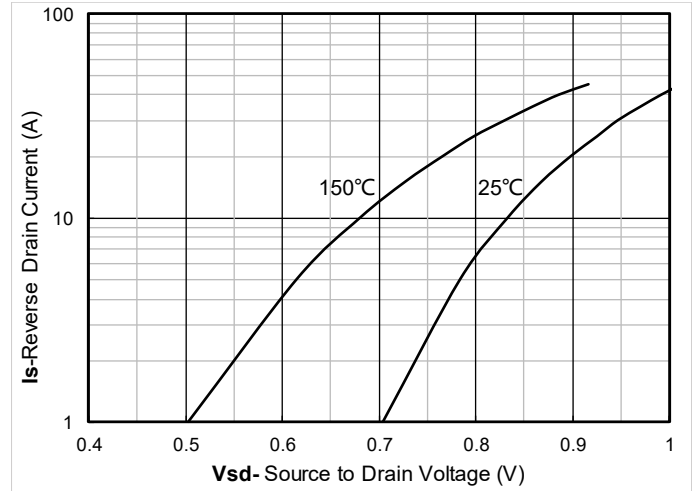


Figure 8. Forward characteristics of reverse diode

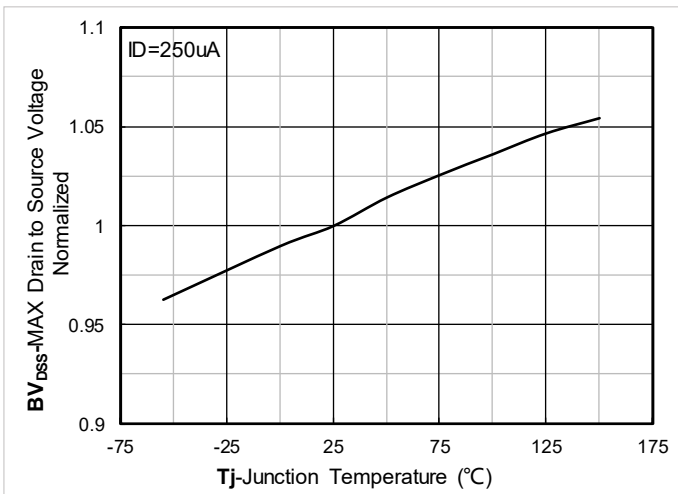


Figure 9. Normalized breakdown voltage

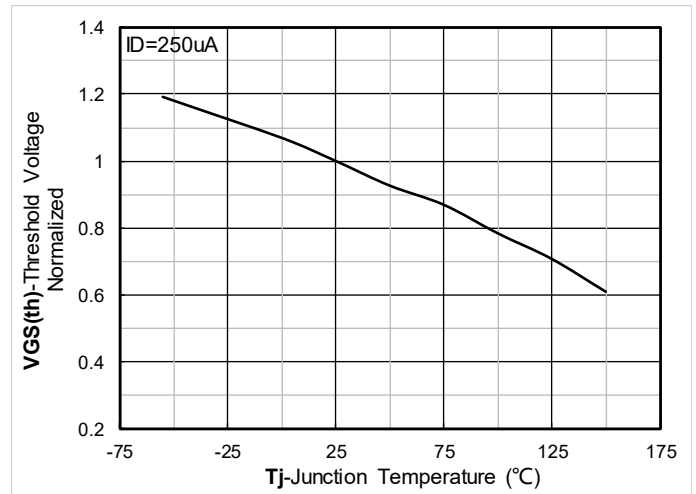


Figure 10. Normalized Threshold voltage

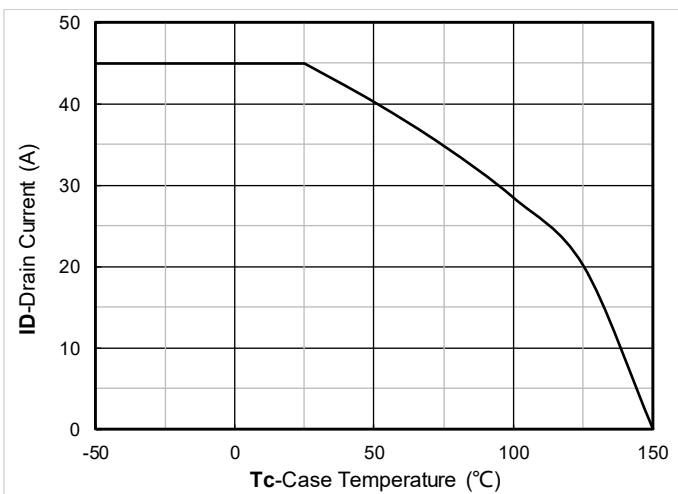


Figure 11. Current dissipation

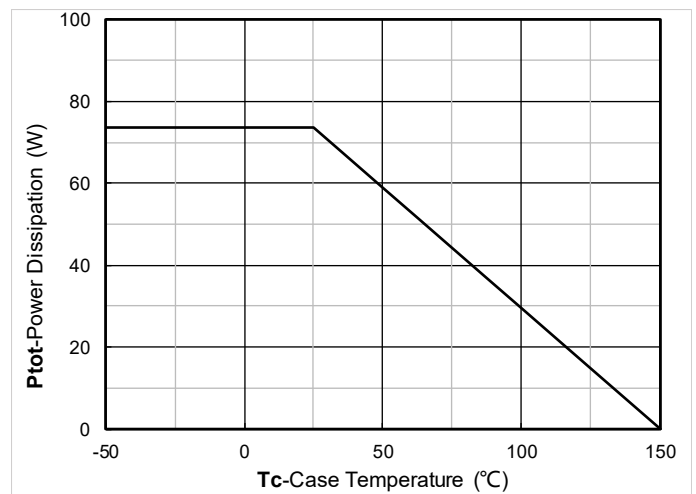


Figure 12. Power dissipation

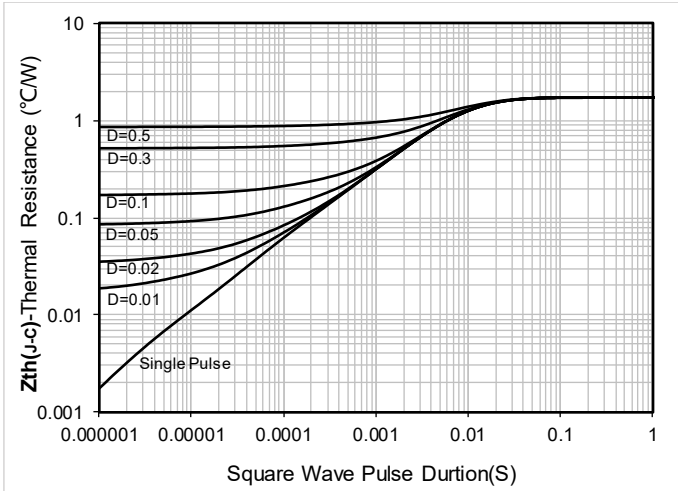


Figure 13. Maximum Transient Thermal Impedance

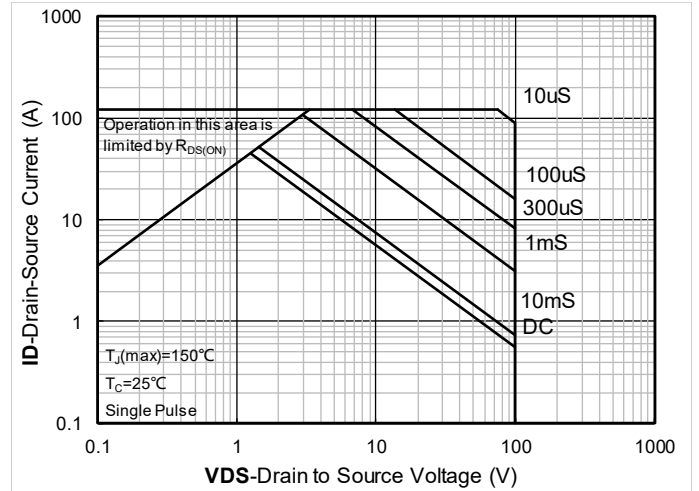


Figure 14. Safe Operation Area

## ■ Test Circuits & Waveforms

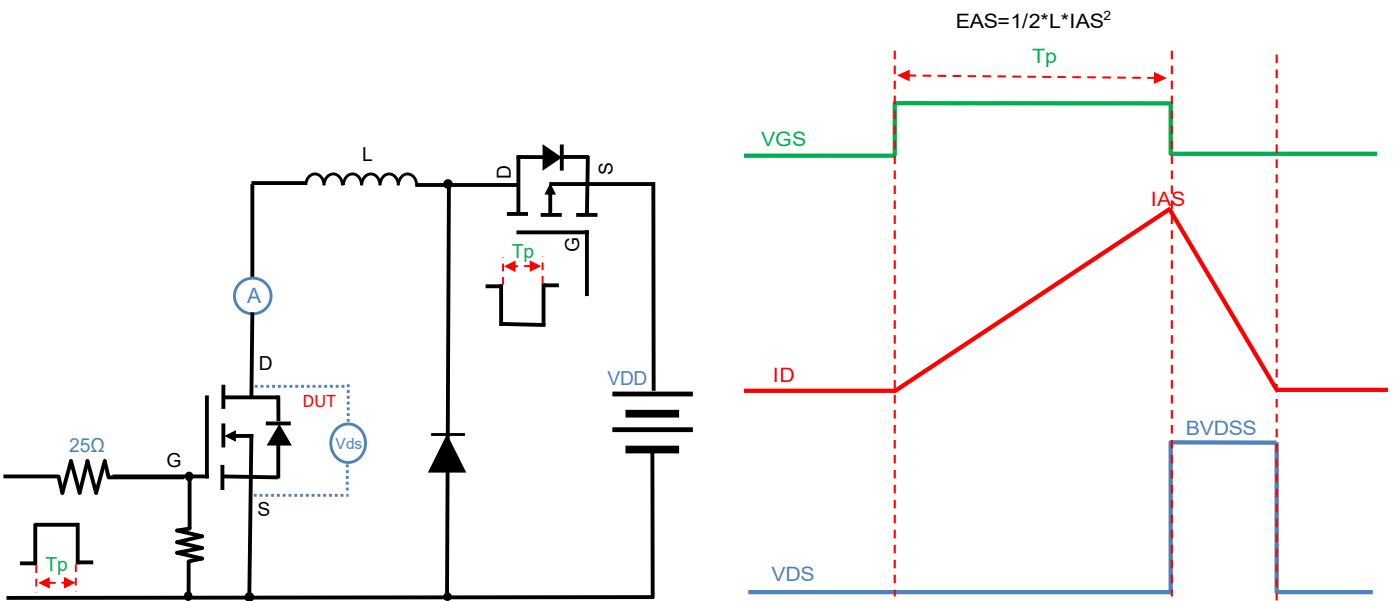


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

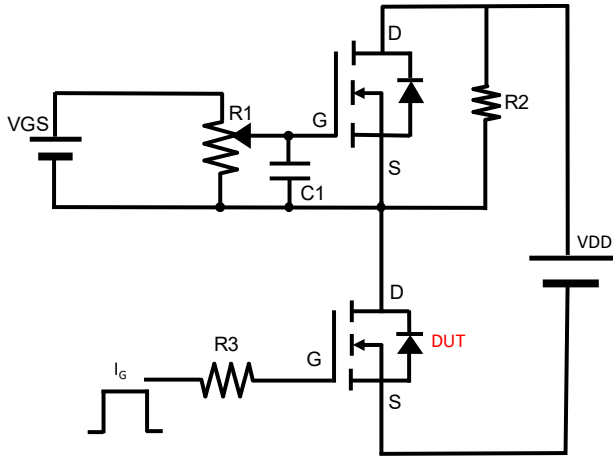


Figure B. Gate Charge Test Circuit & Waveform

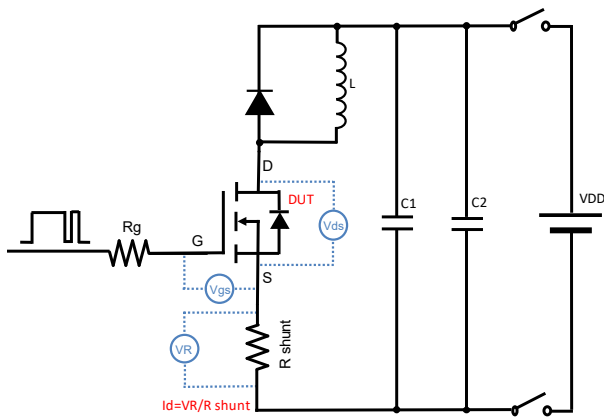


Figure C. Resistive Switching Test Circuit & Waveform

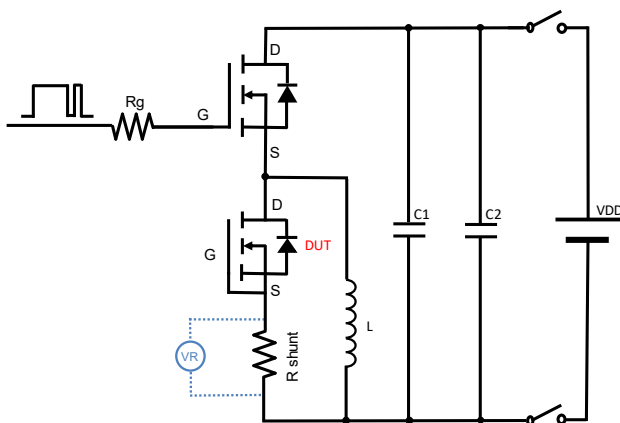
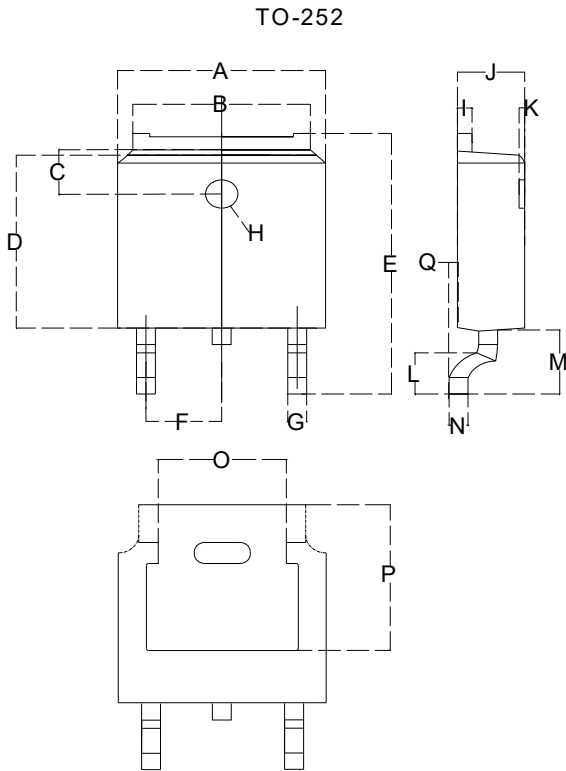


Figure D. Diode Recovery Test Circuit & Waveform



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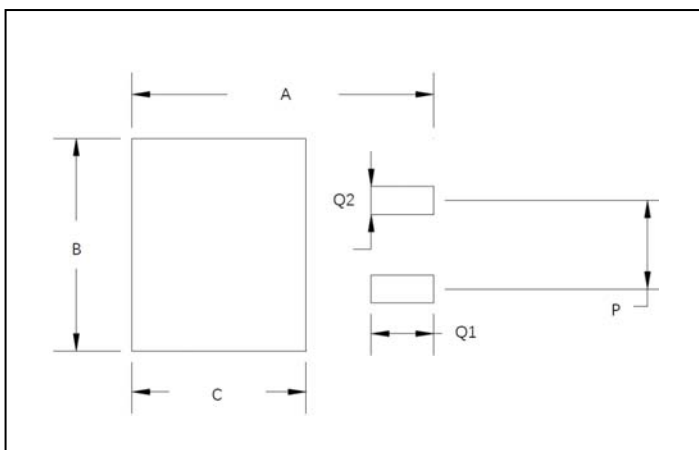
## ■ TO-252 Package information



TO-252		
Dim	Min	Max
A	6.500	6.700
B	5.100	5.460
C	1.400	1.800
D	6.000	6.200
E	10.000	10.400
F	2.166	2.366
G	0.660	0.860
H	Φ1.050	Φ1.350
I	0.460	0.580
J	2.200	2.400
K	0	0.300
L	0.890	2.290
M	2.730	3.080
N	0.430	0.580
O	4.20	4.95
P	5.15	5.45
Q	0	0.2

Dimensions in millimeters

## ■ Suggested Pad Layout



Dim	Millimeters
A	11.4
B	6.74
C	6.23
P	4.56
Q1	2.28
Q2	1.52





## YJD45G10AQ

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